

FEATURES

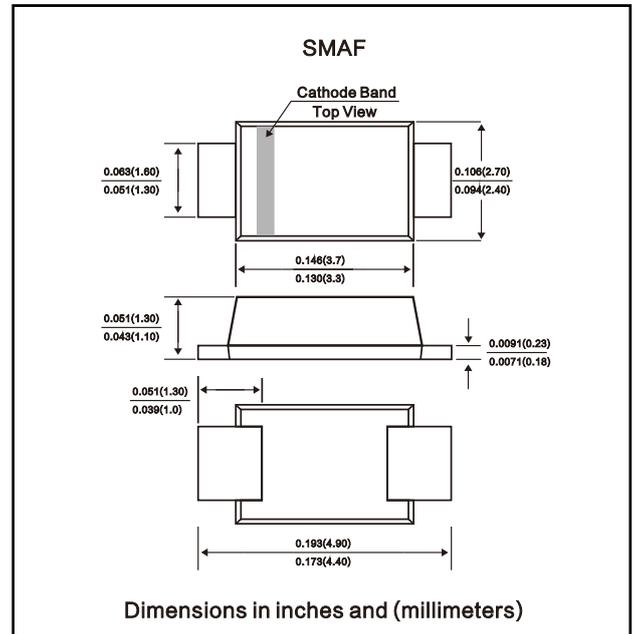
- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 27mg / 0.00095oz

Maximum Ratings and Electrical characteristics

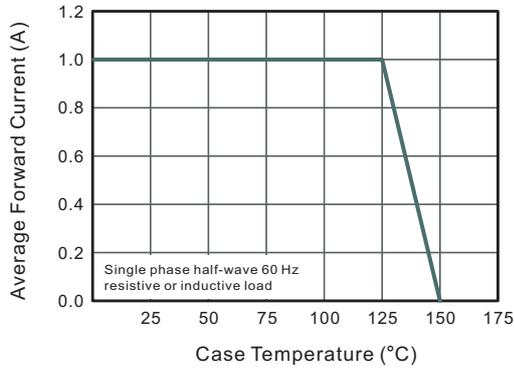
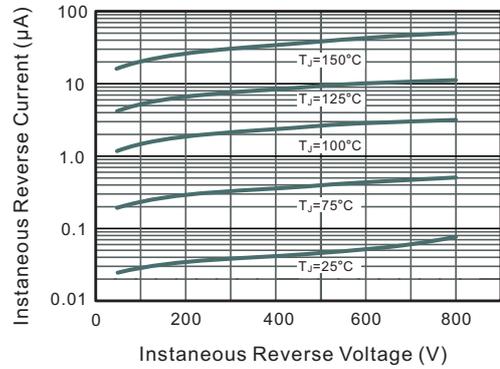
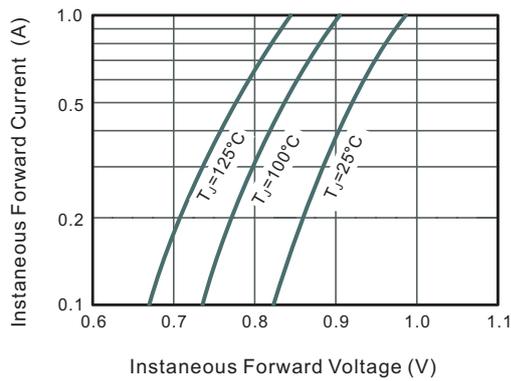
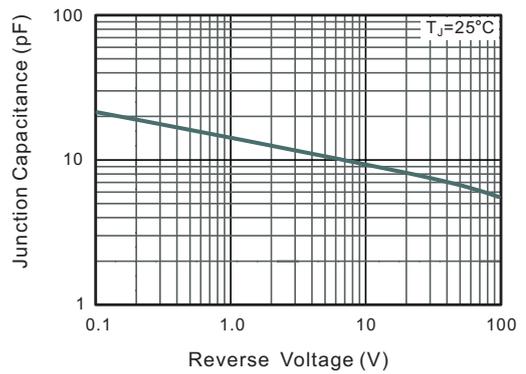
Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.



Parameter	Symbols	S1AF	S1BF	S1DF	S1GF	S1JF	S1KF	S1MF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_c = 125\text{ }^\circ\text{C}$	$I_{F(AV)}$	1							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V_F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_a = 25\text{ }^\circ\text{C}$ $T_a = 125\text{ }^\circ\text{C}$	I_R	5 50							μA
Typical Junction Capacitance ⁽¹⁾	C_j	15							pF
Typical Thermal Resistance ⁽²⁾	$R_{\theta JA}$ $R_{\theta JC}$	80 27							$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							$^\circ\text{C}$

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Fig.1 Forward Current Derating Curve

Fig.2 Typical Instantaneous Reverse Characteristics

Fig.3 Typical Forward Characteristic

Fig.4 Typical Junction Capacitance

Fig.5 Maximum Non-Repetitive Peak Forward Surge Current
